

FIG. 1

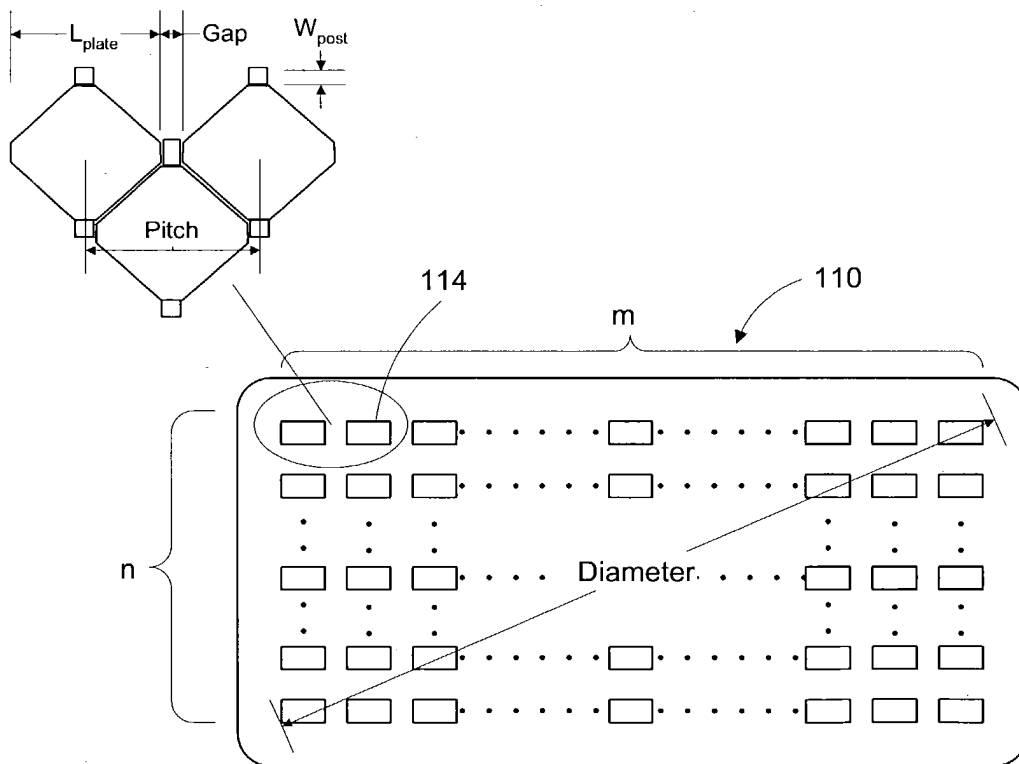


FIG. 2

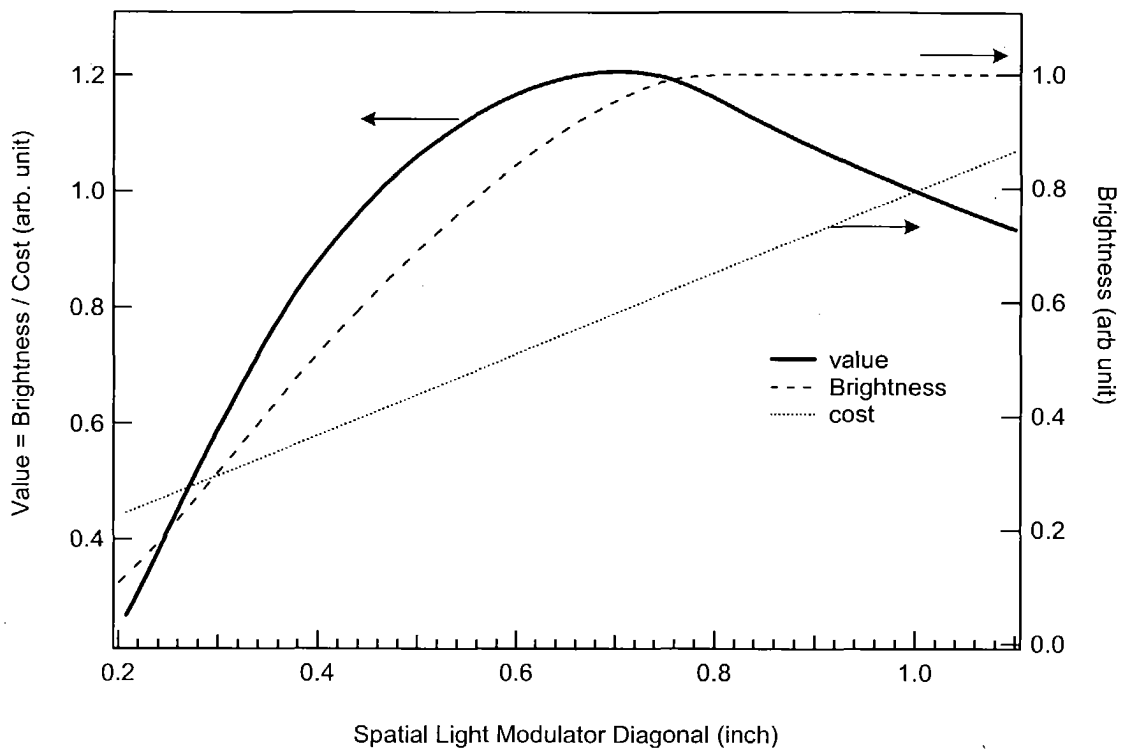


FIG. 3

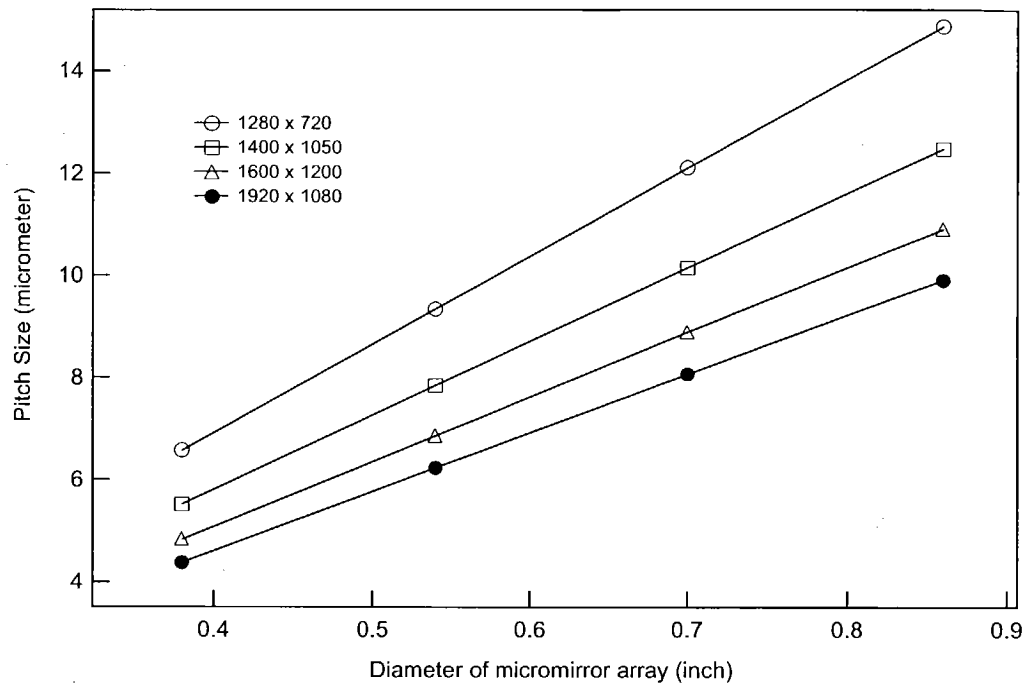


FIG. 4

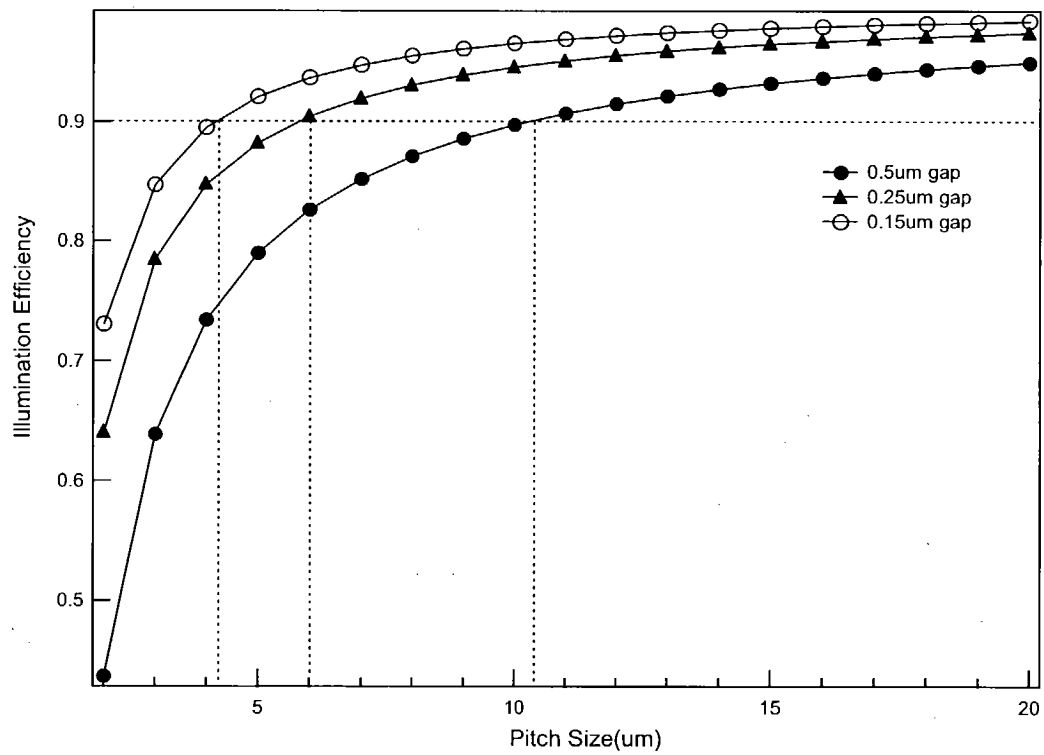


FIG. 5

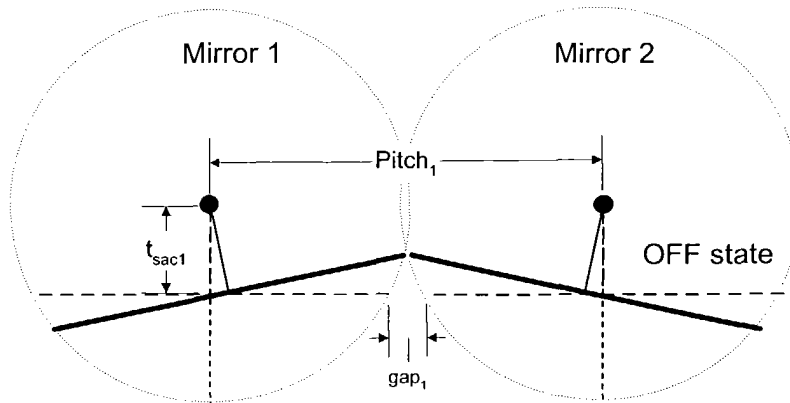


FIG. 6a

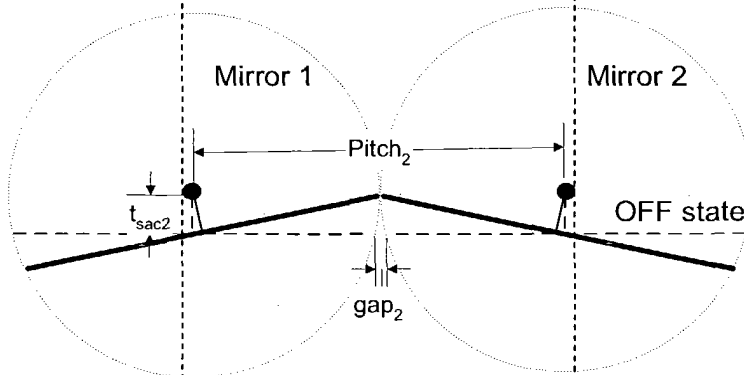


FIG. 6b

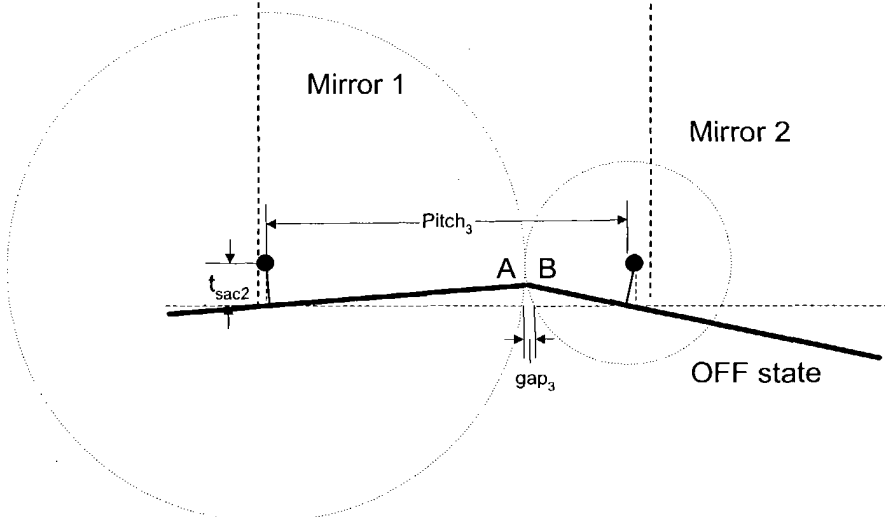


FIG. 6c

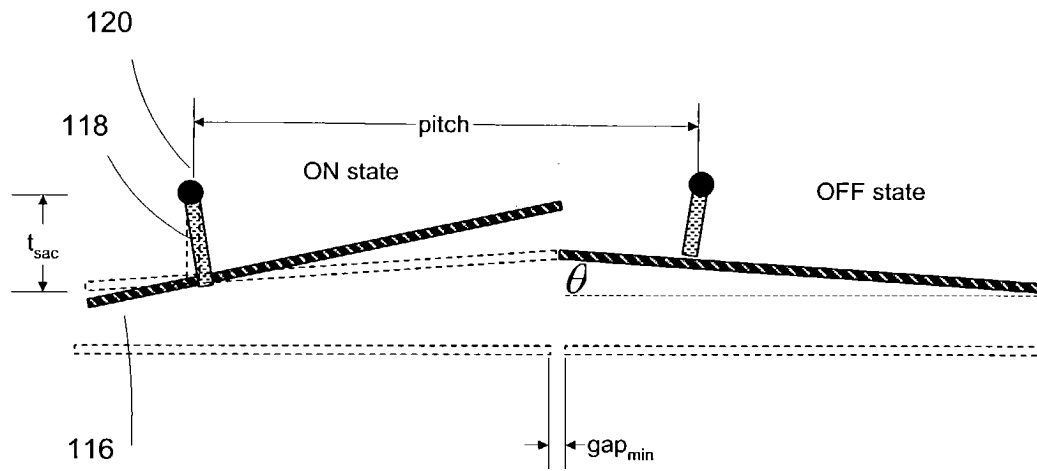


FIG. 7

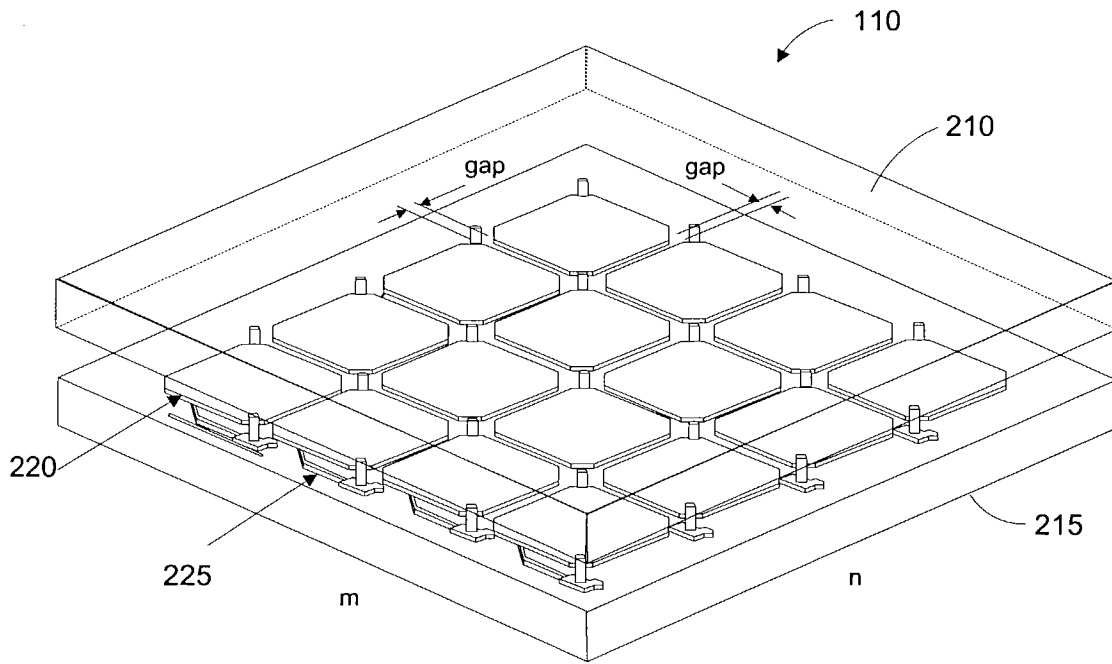


FIG. 8a

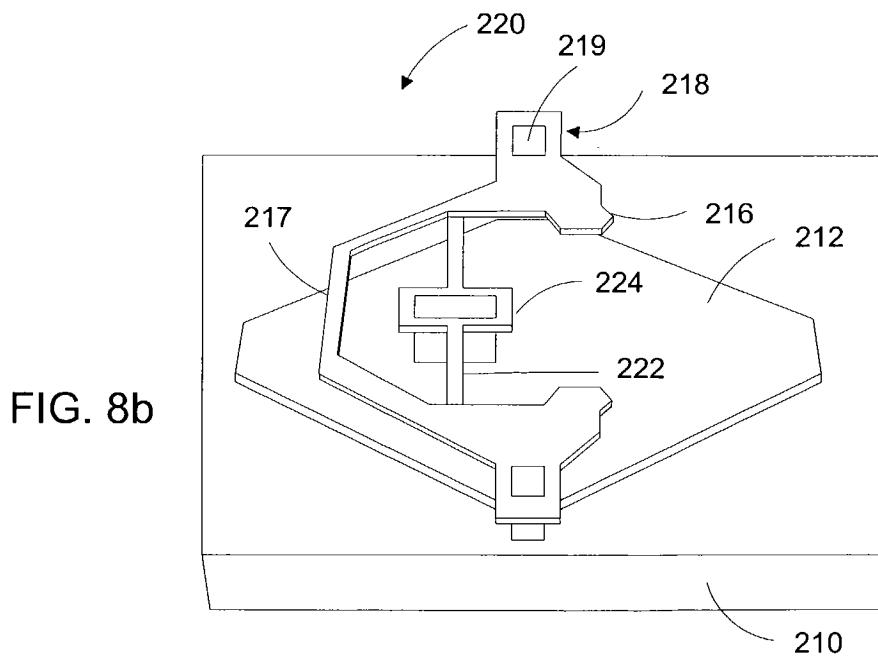


FIG. 8b

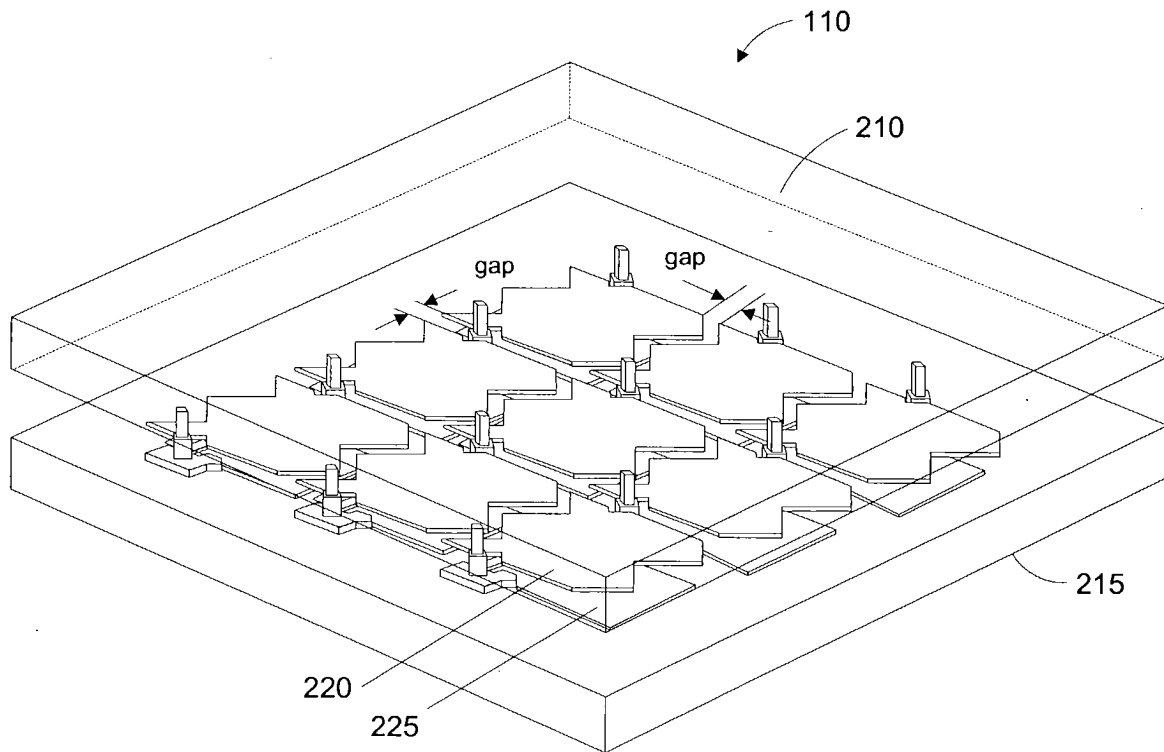


FIG. 9a

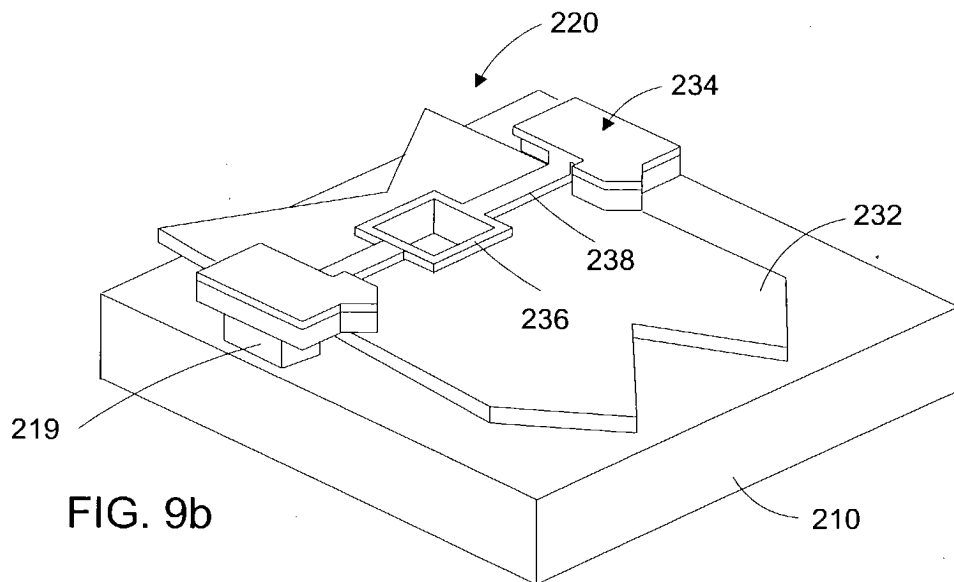


FIG. 9b

A cross-sectional view of a semiconductor device. A central channel region (236) is defined by a thin layer (238) on a substrate. The channel is flanked by side regions (234) which are doped with a different material, indicated by a different hatching pattern. The entire structure is covered by a top layer (236) which is also doped, indicated by a diagonal hatching pattern.

FIG. 10c



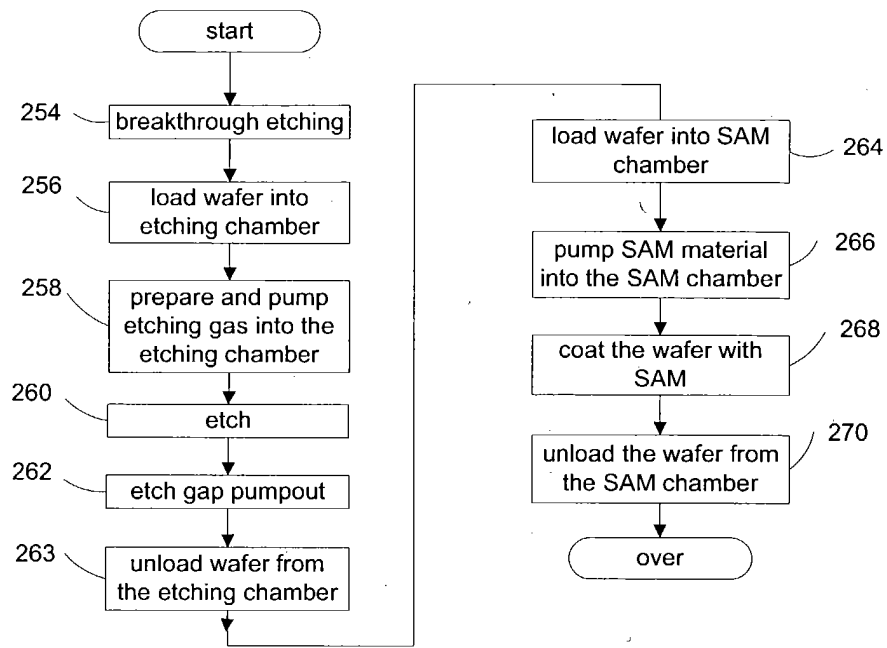


FIG. 11

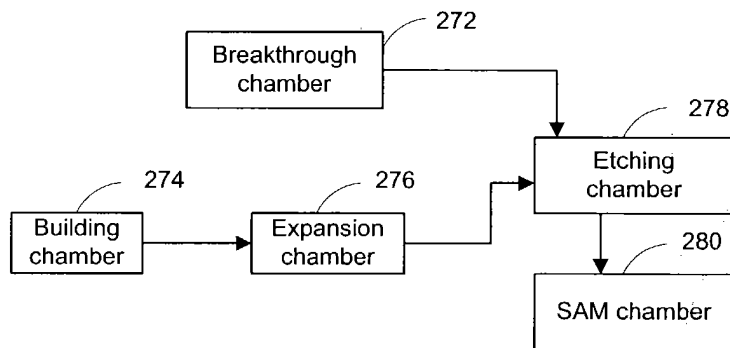


FIG. 12

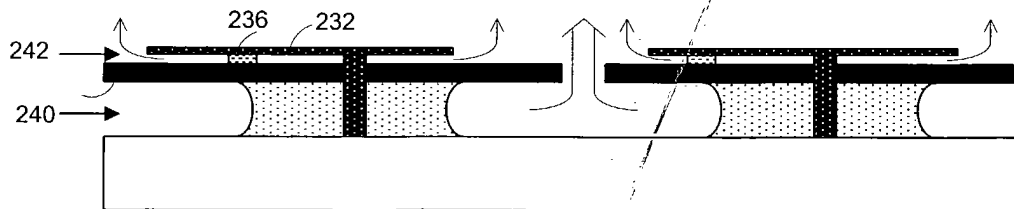


FIG. 13